BCW72LT1G, SBCW72LT1G

General Purpose Transistor

NPN Silicon

ON Semiconductor®

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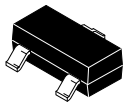
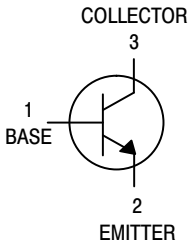


SOT−23
(TO−236)
CASE 318−08
STYLE 6



Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	45	Vdc
Collector−Base Voltage	V_{CBO}	50	Vdc
Emitter−Base Voltage	V_{EBO}	5.0	Vdc
Collector Current − Continuous	I_C	100	mAdc

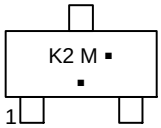
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board, (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR−5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

MARKING DIAGRAM



K2 = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BCW72LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
SBCW72LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Breakdown Voltage (I_C = 2.0 mAdc, V_{EB} = 0)	$V_{(BR)CEO}$	45	–	–	Vdc
Collector−Emitter Breakdown Voltage (I_C = 2.0 mAdc, V_{EB} = 0)	$V_{(BR)CES}$	45	–	–	Vdc
Collector−Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	50	–	–	Vdc
Emitter−Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	–	–	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0) (V_{CB} = 20 Vdc, I_E = 0, T_A = 100°C)	I_{CBO}	– –	– –	100 10	nAdc μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	200	–	450	–
Collector−Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc) (I_C = 50 mAdc, I_B = 2.5 mAdc)	$V_{CE(sat)}$	– –	– 0.21	0.25 –	Vdc
Base−Emitter Saturation Voltage (I_C = 50 mAdc, I_B = 2.5 mAdc)	$V_{BE(sat)}$	–	0.85	–	Vdc
Base−Emitter On Voltage (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)	$V_{BE(on)}$	0.6	–	0.75	Vdc
SMALL−SIGNAL CHARACTERISTICS					
Current−Gain − Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)	f_T	–	300	–	MHz
Output Capacitance (I_E = 0, V_{CB} = 10 Vdc, f = 1.0 MHz)	C_{obo}	–	–	4.0	pF
Input Capacitance (I_E = 0, V_{CB} = 10 Vdc, f = 1.0 MHz)	C_{ibo}	–	9.0	–	pF
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5.0 Vdc, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	–	–	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

EQUIVALENT SWITCHING TIME TEST CIRCUITS

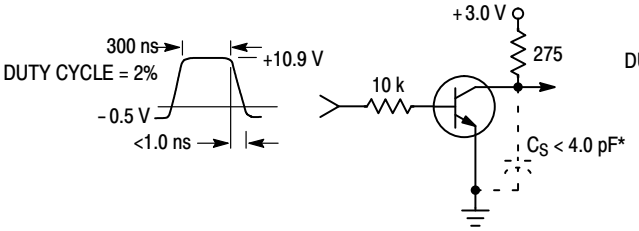


Figure 1. Turn−On Time

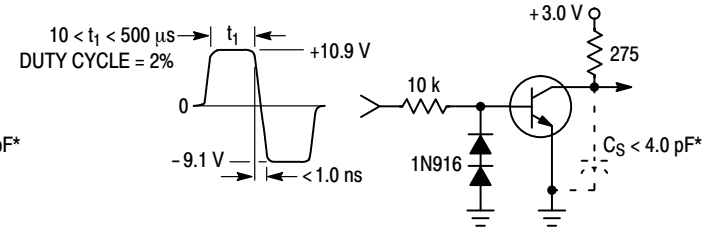


Figure 2. Turn−Off Time

*Total shunt capacitance of test jig and connectors

TYPICAL NOISE CHARACTERISTICS

(V_{CE} = 5.0 Vdc, T_A = 25°C)

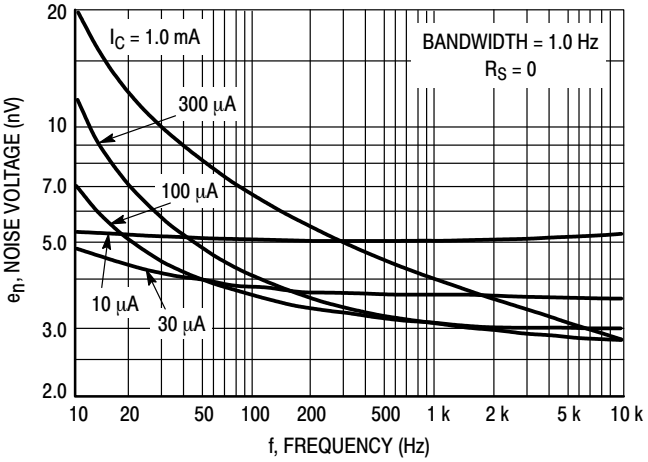


Figure 3. Noise Voltage

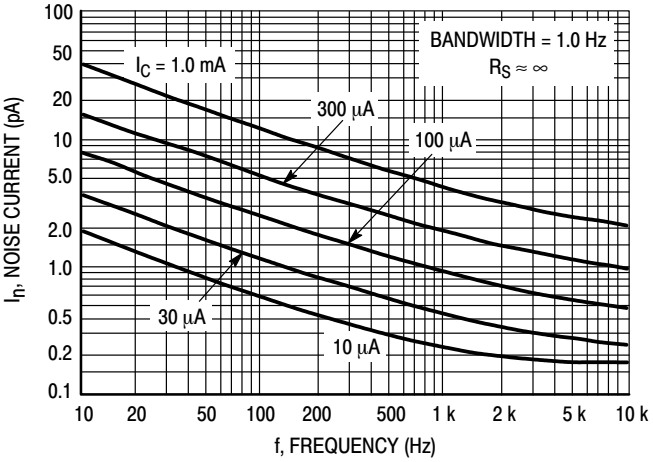


Figure 4. Noise Current

NOISE FIGURE CONTOURS

(V_{CE} = 5.0 Vdc, T_A = 25°C)

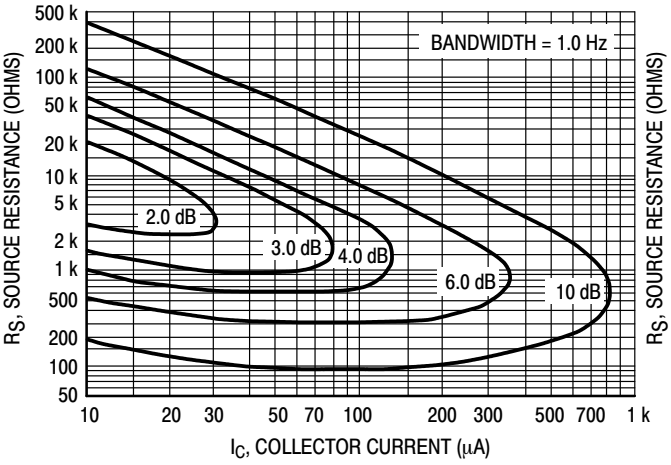


Figure 5. Narrow Band, 100 Hz

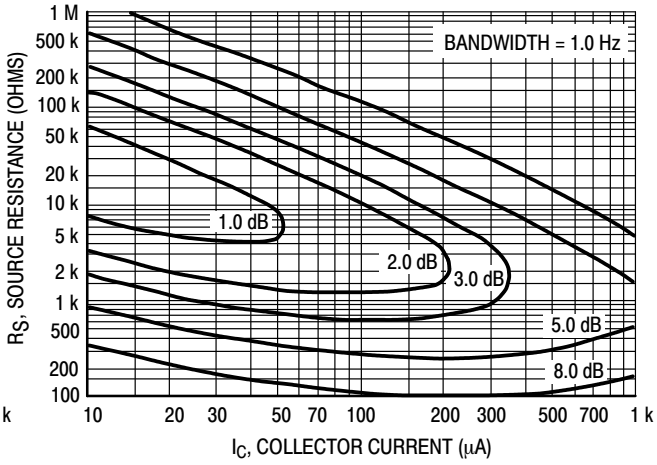


Figure 6. Narrow Band, 1.0 kHz

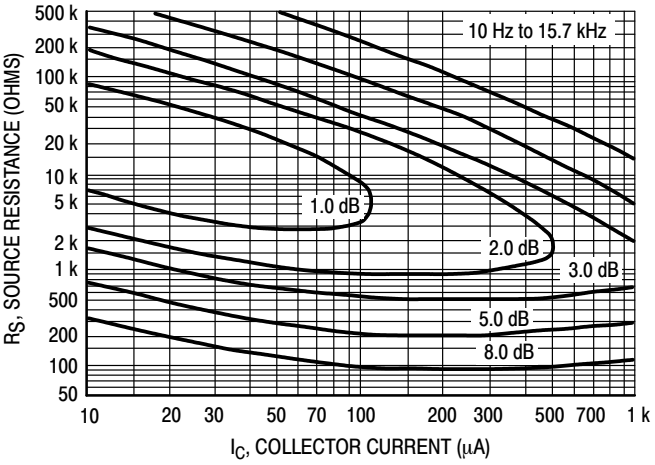


Figure 7. Wideband

Noise Figure is defined as:

$$NF = 20 \log_{10} \left(\frac{e_n^2 + 4KTR_S + I_n^2 R_S^2}{4KTR_S} \right)^{1/2}$$

e_n = Noise Voltage of the Transistor referred to the input. (Figure 3)
I_n = Noise Current of the Transistor referred to the input. (Figure 4)
K = Boltzman's Constant (1.38 x 10^{-23} j/°K)
T = Temperature of the Source Resistance (°K)
R_S = Source Resistance (Ohms)

TYPICAL STATIC CHARACTERISTICS

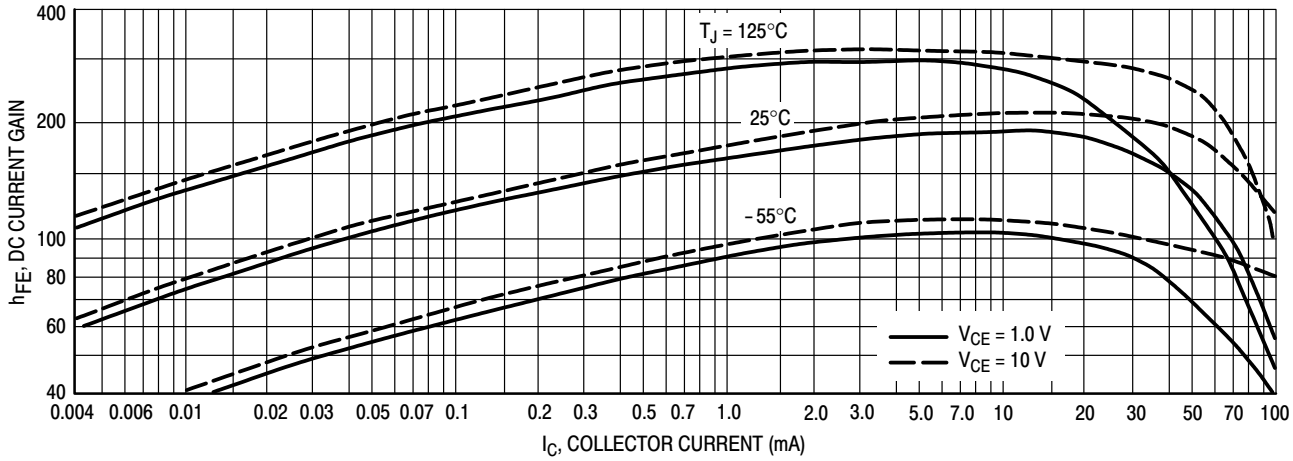


Figure 8. DC Current Gain

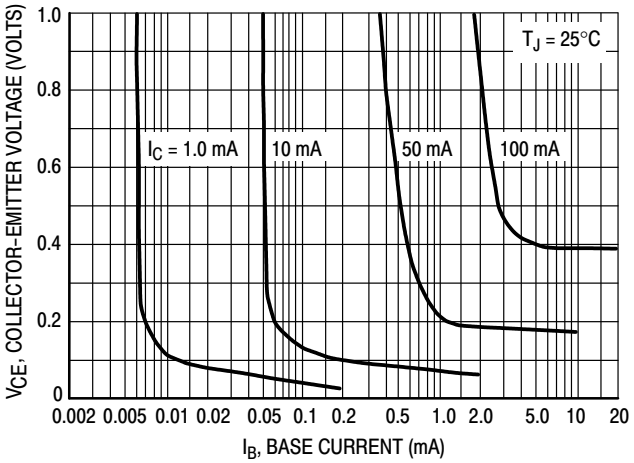


Figure 9. Collector Saturation Region

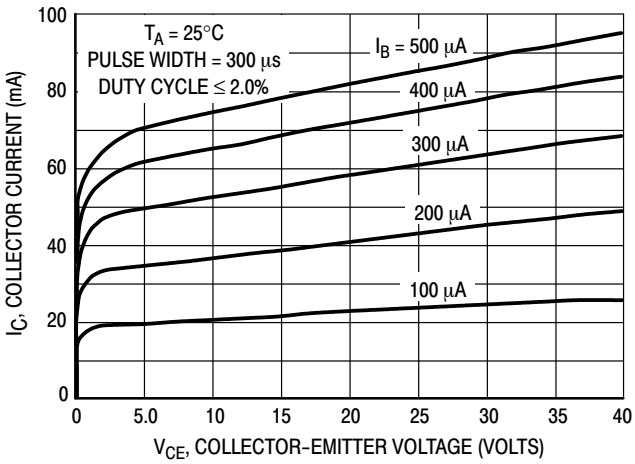


Figure 10. Collector Characteristics

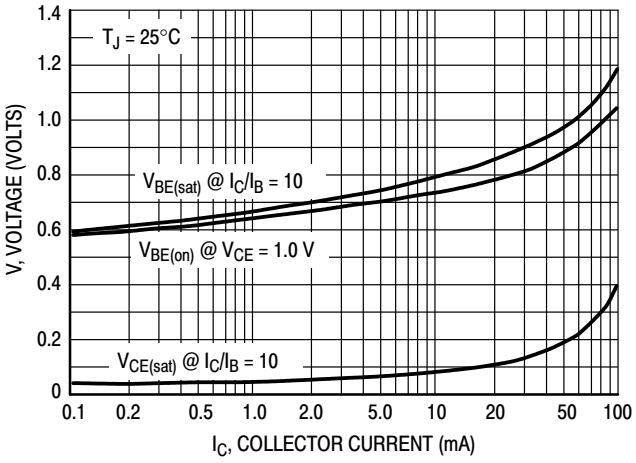


Figure 11. “On” Voltages

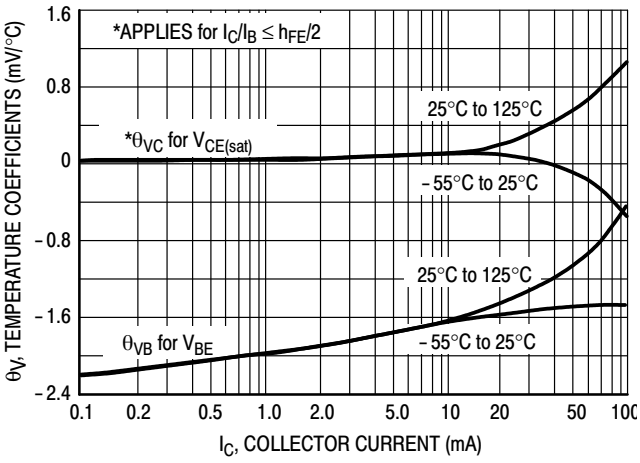


Figure 12. Temperature Coefficients

TYPICAL DYNAMIC CHARACTERISTICS

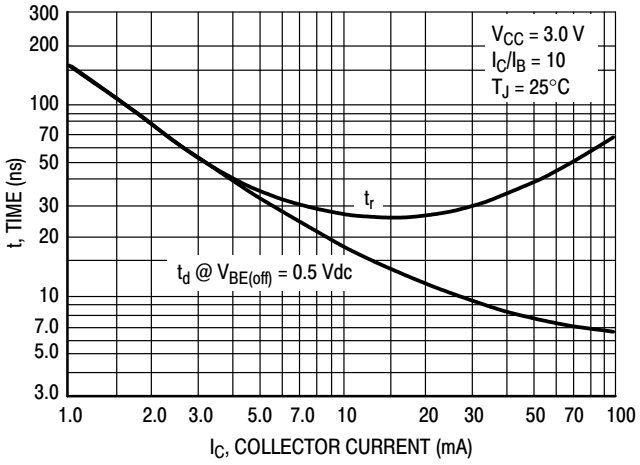


Figure 13. Turn−On Time

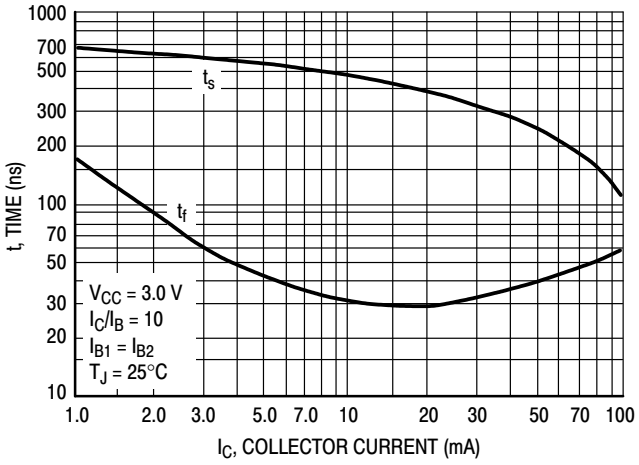


Figure 14. Turn−Off Time

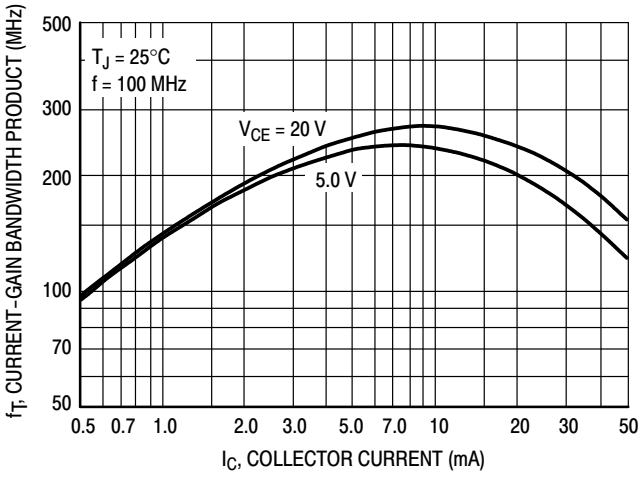


Figure 15. Current−Gain — Bandwidth Product

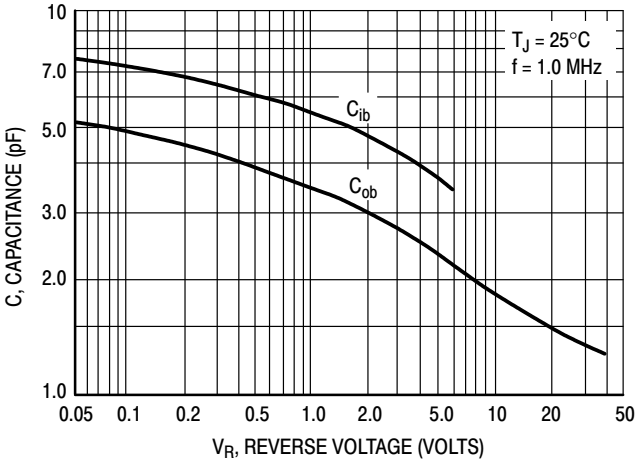


Figure 16. Capacitance

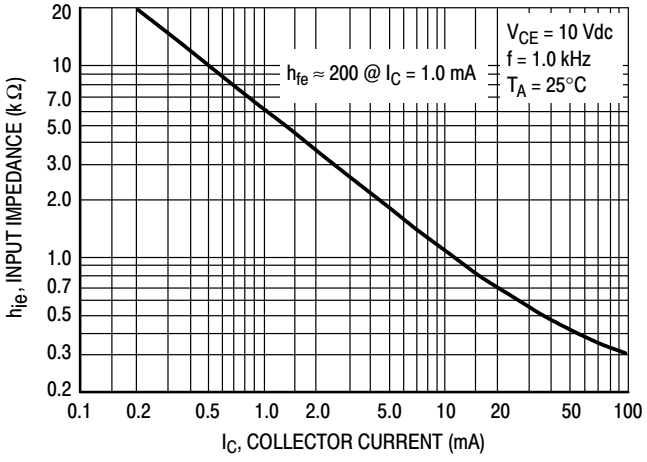


Figure 17. Input Impedance

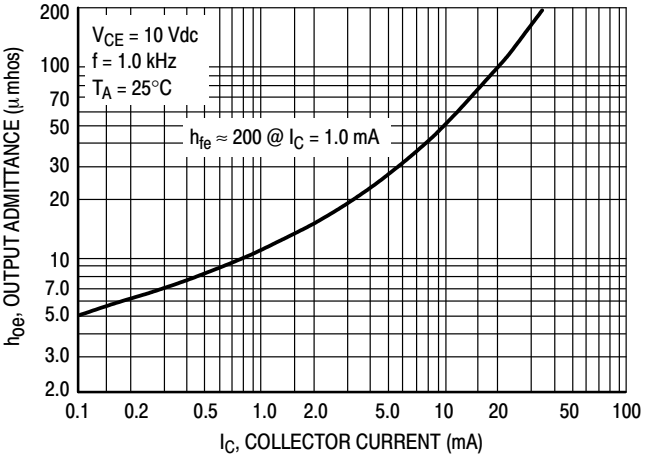


Figure 18. Output Admittance

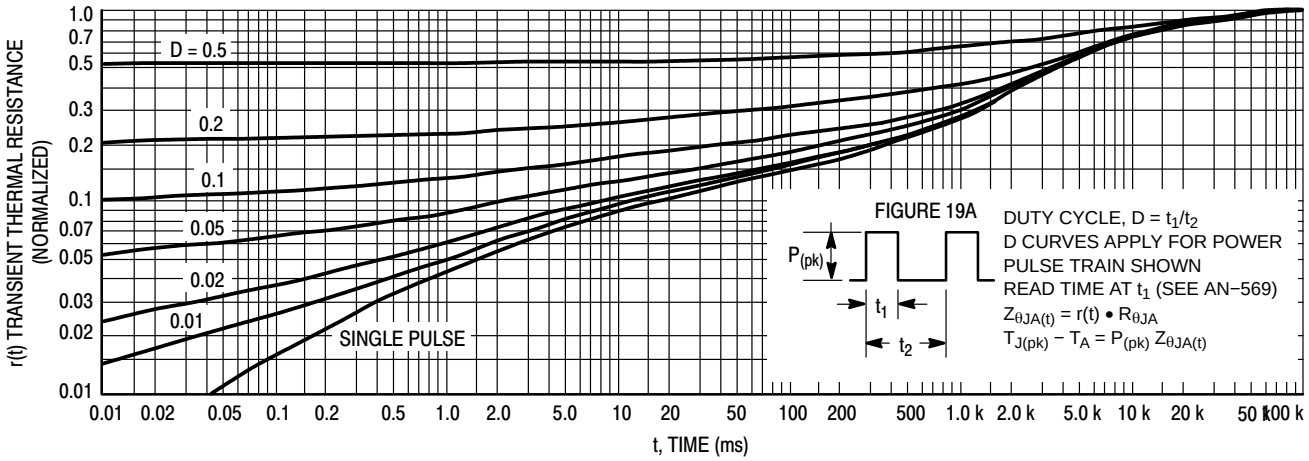


Figure 19. Thermal Response

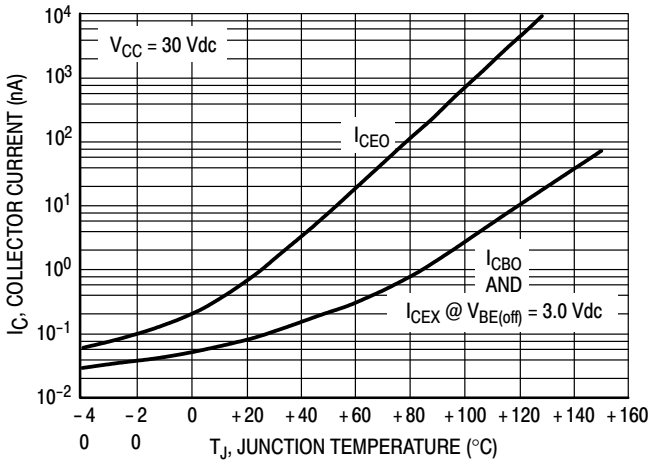


Figure 19A.

DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 19A. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 19 was calculated for various duty cycles.

To find $Z_{\theta JA(t)}$, multiply the value obtained from Figure 19 by the steady state value $R_{\theta JA}$.

Example:

The MPS3904 is dissipating 2.0 watts peak under the following conditions:

t_1 = 1.0 ms, t_2 = 5.0 ms. (D = 0.2)

Using Figure 19 at a pulse width of 1.0 ms and D = 0.2, the reading of r(t) is 0.22.

The peak rise in junction temperature is therefore

$\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88°C$.

For more information, see AN−569.

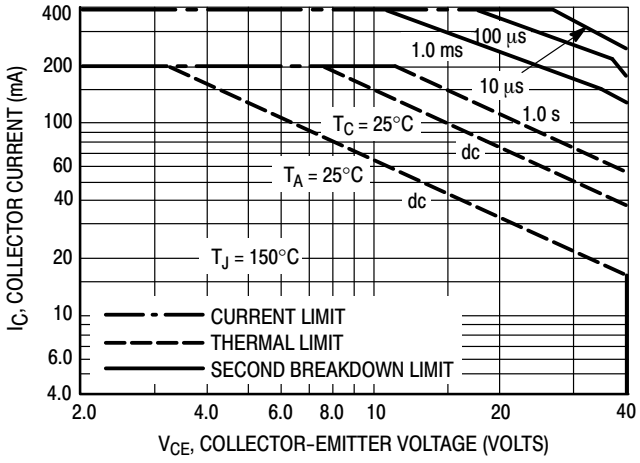


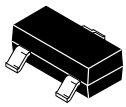
Figure 20.

The safe operating area curves indicate I_C−V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 20 is based upon $T_{J(pk)}$ = 150°C; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \le 150°C$. $T_{J(pk)}$ may be calculated from the data in Figure 19. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

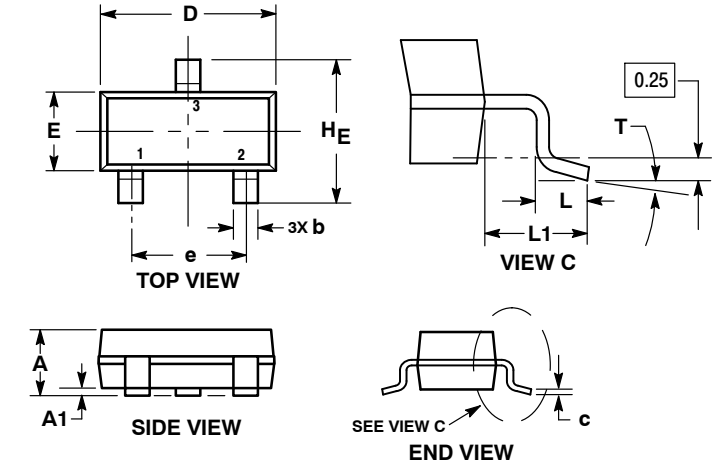
ON Semiconductor®



SOT−23 (TO−236)
CASE 318−08
ISSUE AS

DATE 30 JAN 2018

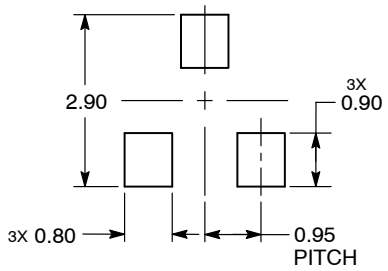
SCALE 4:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

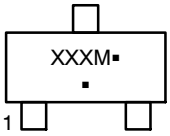
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	−−−	10°	0°	−−−	10°

RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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DESCRIPTION:	SOT−23 (TO−236)	PAGE 1 OF 1

PUBLICATION ORDERING INFORMATION

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Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

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